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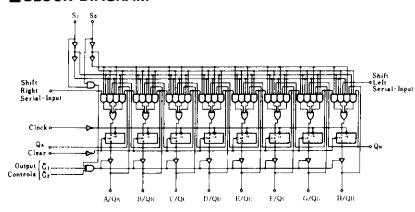
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This eight-bit universal register features multiplexed inputs/ outputs to achieve full eight bit data. Two function-select inputs and two output-control inputs can be used to choose the modes of operation listed in the function table.

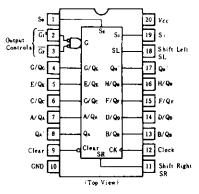
Synchronous parallel loading is accomplished by taking both function select lines, S_0 and S_1 , high. This places the three-

state outputs in a high-impedance state, which permits data that is applied on the input/output lines to be clocked into the register. Reading out of the register can be accomplished while the outputs are enabled in any mode. A direct overriding input is provided to clear the register whether the outputs are enabled or off.

■ BLOCK DIAGRAM



■ PIN ARRANGEMENT



MABSOLUTE MAXIMUM RATINGS

ltem	Symbol	Ratings	Unit	
Supply voltage	Vec	7.0	V	
Input voltage	V_{IN}	7.0	V	
Output voltage (off-state)	Voieff	5.5	v	
Operating temperature range	T.,.	-20~+75	°C	
Storage temperature range	T.c.	-65~+150	°C	

FUNCTION TABLE

		Inputs					Inputs/Outputs							Outputs				
Mode	Clear	Function Select		1		Clock: Serial	rial	A/Q _A	B/Q _B	C/Qc	D/Q _D	E/Q _E	F/Q _F	G/Q _G	H/Q _H	Q _A '	Q _H ′	
		S	So	Ū₁ t	G, t		Ş۱	S _R	R									
СІевг	L	×	L	L	L	×	×	×	L	L	L	L	L	L	L	L	L	L
Clear	L	L	×	L	L	×	×	×	L	L	L	L	L	L	L	L	L	L
Hold	Н	L	L	L	L	×	×	×	QAO	QBO	Qco	\mathbf{Q}_{DO}	QEO	QFO	Qco	Qно	QAO	Q _{HO}
нога	Н	×	×	L	L	L	×	×	QAO	Qao	Qco	Q_{DO}	QEO	QFO	Qco	Qно	QAO	QHO
Chife Diele	Н	L	Н	L	L	1	×	Н	Н	QAh	Q _B ,	Qcn	Q _D ,	Q _E ,	Qr.	Qcn	Н	Q _G
Shift Right	Н	L	Н	L	L,	†	×	L	L	Q _A ,	Q _B ,	Qcn	Q_{Dn}	Q _E	Q_{Fn}	Q _G	L	Q _G ,
Clife I to	Н	Н	L	L	L	t	Н	×	Q _B ,	Qc.	Q _D ,	Q _E	QFs	Qc,	Q _H ,	н	Q _B ,	Н
Shift Left	Н	Н	L	L	L	1	L	×	Q _B ,	Q _C ,	Q_{D_n}	Q _E ,	Qr.	QGA	Q _H	L	Q _B ,	L
Load	Н	H	Н	×	×	1	×	×	а	ь	c	ď	e	f	g	h	a	h

- Notes) 1. H; high level, L; low level, X; irrelevant
 - 2. †; transition from low to high level
 - a~h; the level of steady-state input at inputs A through H,
 respectively. These data are loaded into the flipflop outputs are isolated from the input/output
 terminals.
 - QAo~QH0; the level of QA through QH, respectively, before the indicated steady-state input conditions were established.
- Q_{An}~Q_{Hn}; the level of Q_A through Q_H, respectively, before the most-recent † transition of the clock.
- 6. † =; When one or both output controls are high the eight input/output terminals are desabled to the high-impedance state, however, sequential operation or clearing of the register is not affected.

RECOMMENDED OPERATING CONDITIONS

I :	tem	Symbol	min	typ	max	Unit
	Q _A Q _H				-2.6	mA
Output current	QA' OF QH'	Ion	_		-0.4	
	Q _A ~Q _H		_		24	mA
Output current	QA' or QH'	- IoL	-	_	8	1111
Clock frequency		Jeinek .	0		25	MHz
	Clock high		30	_		ns
Clock pulse width	Clock low	tw(CK)	10			113
Clear pulse width	Clear low	tw(CLR)	20			ns
	Select		35 t			
	High-level data	,	20 †			n.s
Setup time	Low-level data	t	20 †			""
	Clear inactive-state		20 †			
Hold time	Select		10 t	l		ns
	Data	t,	10 t		<u> </u>	

t The arrow indicates the rising edge.

ELECTRICAL CHARACTERISTICS $(Ta = -20 \sim +75 ^{\circ}\text{C})$

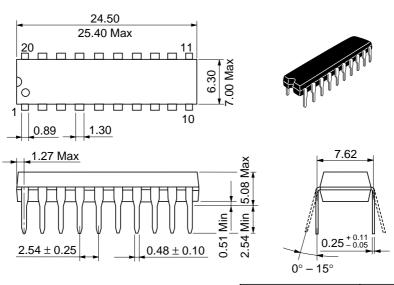
Item		Symbol	Test Conditi	min	typ*	max	Unit	
Item		VIH			2.0	_		V
Input voltage		V_{IL}			_		0.8	V
	QA thru QR		$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V},$	Ion = -2.6mA	2.4			v
	QA' OF QH'	Von	$V_{ii} = 0.8V$	$I_{0H} = -400 \mu A$	2.7			
Output voltage				IoL - 12mA	_		0.4	v
	QA thru QH		Vcc-4.75V	$I_{OL} = 24 \text{mA}$			0.5	
		Vol	$V_{tH}=2V$	$I_{OL} = 4 \text{mA}$			0.4	
	QA' or QH'		$V_{iL}=0.8V$	IoL-8mA	-		0.5	
	QA thru Qu	Iozn	$V_{CC} = 5.25 \text{V}, V_{IN} = 2 \text{V}, V_{O} =$	-2.7V	-		40	μ
Output current	QA thru QH	Iozz	$V_{cc} = 5.25 \text{V}, V_{IH} = 2 \text{V}, V_{o} = 0.00 \text{V}$		-		-400	μ.
So, S1, A	So, Su, A~H			-		40	μ.	
	Any other	Im	$V_{cc}-5.25V, V_{l}-2.7V$	_	_	20	<u>μπ</u>	
	So, Si	IIL				-0.8	mA	
Input current	Any other		$V_{cc} = 5.25 \text{V}, V_{l} = 0.4 \text{V}$	_		-0.4		
Input Carrent	S _b , S ₁	 		V ₁ =7V	_		0.2	
	A~H	I_I	Vcc=5.25V	V ₁ =5.5V			0.1	m.A
	Any other	† -"		V ₁ =7V		[_ _	0.1	
Short-circuit	QA thru QH				-30		-130	m.
output current	QA' or QH'	Ios	Vcc=5.25V		-20		-100	
Supply current	424 4. 474	Icc	Vcc-5.25V			33	53	m.
Input clamp volt	NGA	VIK	$V_{CC} = 4.75 \text{V}, I_{IN} = -18 \text{mA}$				-1.5	1

^{*} V_{CC} = 5V, Ta = 25°C

ESWITCHING CHARACTERISTICS $(V_{cc}=5V, Ta=25^{\circ}C)$

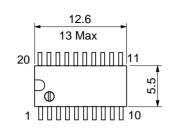
Item	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit
Maximum clock frequency	f=+x	<u> </u>	1		25	35		MHz
Propagation delay time	1 PLH	Clock Qa' or Qu'		6 15 E B -210	_	22	33	
	1 PHL		$C_{L}-15 \text{pF}, R_{L}-2 \text{k}\Omega$	_	26	39	ns	
	tpuL	Clear	QA' or QH'			27	40	
	LPLH		Q _A ~Q _H	$C_L = 45 \text{pF}, R_L = 665 \Omega$	_	17	25	ns
	I PH L	Clock				26	39	
	tpuL	Clear	Q _A ~Q _H			26	40	ns
· · · · · · · · · · · · · · · · · · ·	t zn	t	Q _A ~Q _H		-	13	21	ns
Output enable time	tzı	₹ G₁, G₂				19	30	
Output disable time	t HZ	 	Q _A ~Q _H		_	10	15	
	112	$\overline{G}_1, \overline{G}_2$		C_L -5pF, R_L -665 Ω		10	15	ns ns

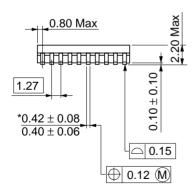
Unit: mm

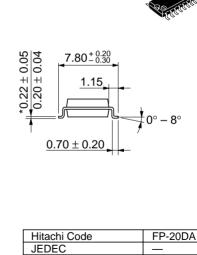


Hitachi Code	DP-20N
JEDEC	_
EIAJ	Conforms
Weight (reference value)	1.26 g

Unit: mm







Weight (reference value)

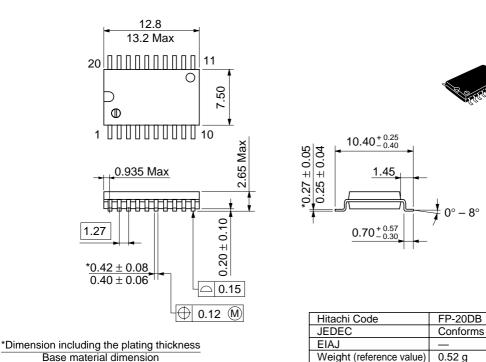
Conforms

0.31 g

EIAJ

*Dimension including the plating thickness
Base material dimension

Unit: mm



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Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road

Maidenhead Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000 Fax: <44> (1628) 778322 Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666

Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218

Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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